

# Subir Parui

## List of Publications by Year in descending order

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24  
papers

582  
citations

840776

11  
h-index

642732

23  
g-index

24  
all docs

24  
docs citations

24  
times ranked

1159  
citing authors

#	ARTICLE	IF	CITATIONS
1	A molecular spin-photovoltaic device. <i>Science</i> , 2017, 357, 677-680.	12.6	147
2	Gate-tunable diode and photovoltaic effect in an organic 2D layered material n junction. <i>Nanoscale</i> , 2015, 7, 15442-15449.	5.6	84
3	Gate-Controlled Energy Barrier at a Graphene/Molecular Semiconductor Junction. <i>Advanced Functional Materials</i> , 2015, 25, 2972-2979.	14.9	58
4	Temperature dependent transport characteristics of graphene/n-Si diodes. <i>Journal of Applied Physics</i> , 2014, 116, .	2.5	53
5	Energy Level Alignment at Metal/Solution-Processed Organic Semiconductor Interfaces. <i>Advanced Materials</i> , 2017, 29, 1606901.	21.0	37
6	Spin doping using transition metal phthalocyanine molecules. <i>Nature Communications</i> , 2016, 7, 13751.	12.8	30
7	Graphene as an electrode for solution-processed electron-transporting organic transistors. <i>Nanoscale</i> , 2017, 9, 10178-10185.	5.6	30
8	Probing electron transport across a LSMO/Nb:STO heterointerface at the nanoscale. <i>Physical Review B</i> , 2013, 87, .	3.2	17
9	Hot electron transport in a strongly correlated transition-metal oxide. <i>Scientific Reports</i> , 2013, 3, 1274.	3.3	16
10	Hot Electrons and Hot Spins at Metal-Organic Interfaces. <i>Advanced Functional Materials</i> , 2018, 28, 1706105.	14.9	12
11	Robust Spin Interconnect with Isotropic Spin Dynamics in Chemical Vapor Deposited Graphene Layers and Boundaries. <i>ACS Nano</i> , 2020, 14, 15864-15873.	14.6	12
12	Nanoscale hot electron transport across Cu/n-Si(100) and Cu/n-Si(111) interfaces. <i>Physica Status Solidi - Rapid Research Letters</i> , 2011, 5, 388-390.	2.4	10
13	Hot electron transmission in metals using epitaxial NiSi <sub>2</sub> /n-Si(111) interfaces. <i>Applied Physics Letters</i> , 2011, 99, 032104.	3.3	10
14	Frequency driven inversion of tunnel magnetoimpedance and observation of positive tunnel magnetocapacitance in magnetic tunnel junctions. <i>Applied Physics Letters</i> , 2016, 109, 052401.	3.3	10
15	Probing hot electron transport across an epitaxial Schottky interface of SrRuO <sub>3</sub> /Nb:SrTiO <sub>3</sub> . <i>Applied Physics Letters</i> , 2013, 102, .	3.3	8
16	Reliable determination of the Cu/n-Si Schottky barrier height by using in-device hot-electron spectroscopy. <i>Applied Physics Letters</i> , 2015, 107, .	3.3	8
17	Strain Effects on the Energy-Level Alignment at Metal/Organic Semiconductor Interfaces. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 12717-12722.	8.0	8
18	Comparison of hot-electron transmission in ferromagnetic Ni on epitaxial and polycrystalline Schottky interfaces. <i>Physical Review B</i> , 2012, 85, .	3.2	7

#	ARTICLE	IF	CITATIONS
19	Gate-tunable graphene-organic interface barrier for vertical transistor and logic inverter. Applied Physics Letters, 2018, 113, .	3.3	7
20	Molecular spectroscopy in a solid-state device. Materials Horizons, 2019, 6, 1663-1668.	12.2	7
21	Top dielectric induced ambipolarity in an n-channel dual-gated organic field effect transistor. Journal of Materials Chemistry C, 2019, 7, 10389-10393.	5.5	5
22	Hot electron attenuation of direct and scattered carriers across an epitaxial Schottky interface. Journal of Physics Condensed Matter, 2013, 25, 445005.	1.8	3
23	Evidence of spin scattering and collection of hot electrons at different conduction minima in Si. Applied Physics Letters, 2013, 103, 082409.	3.3	2
24	Spin transport in metal and oxide devices at the nanoscale. , 2012, , .		1